



# FMMT493

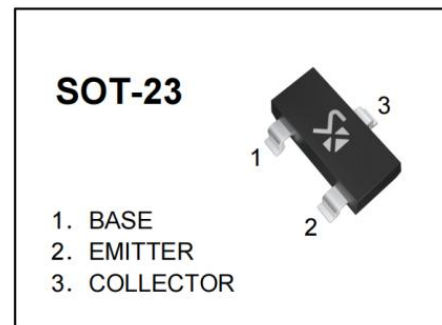
## NPN Silicon Epitaxial Planar Transistor

### Features

- Complimentary to FMMT593

### Marking:493

### Maximum Ratings( $T_A=25^{\circ}\text{C}$ , unless otherwise noted.)



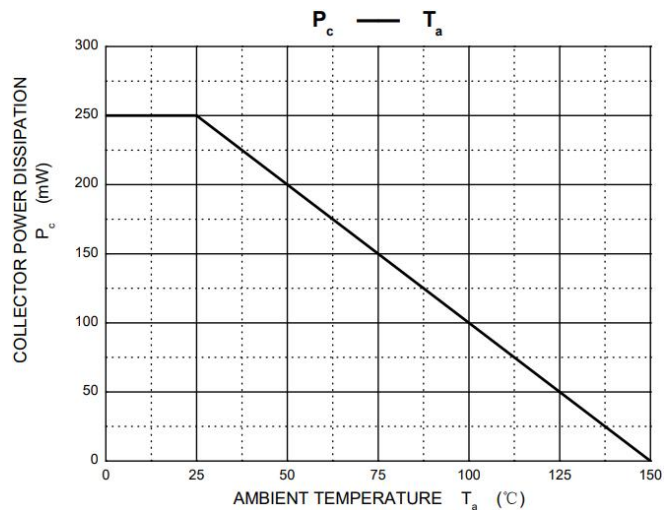
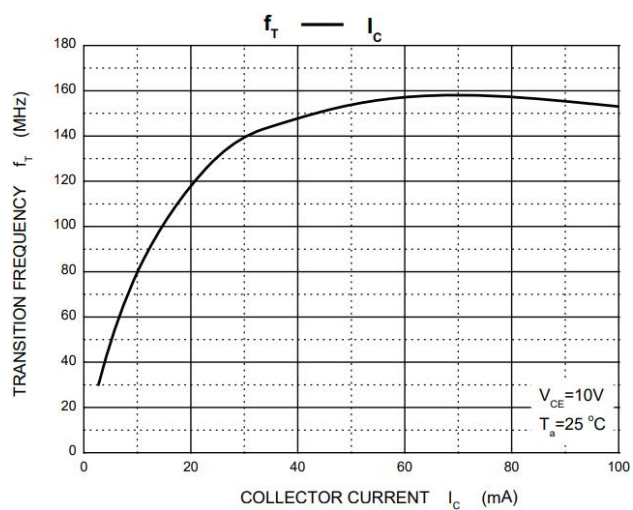
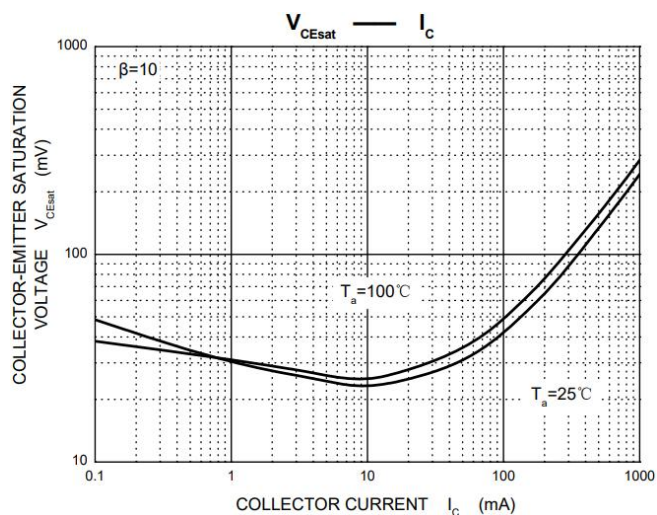
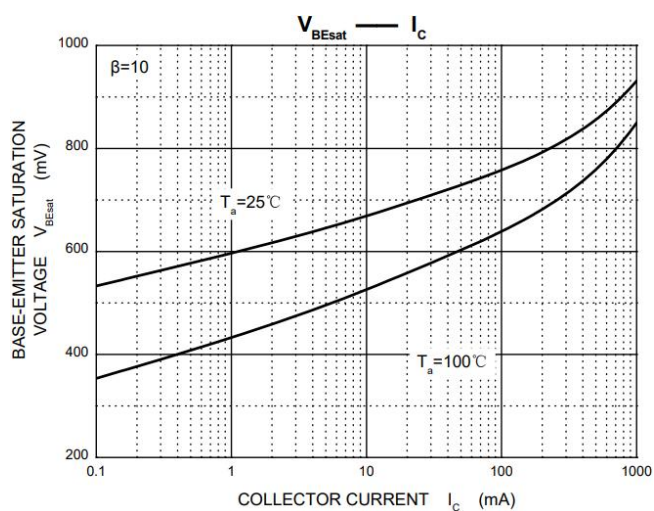
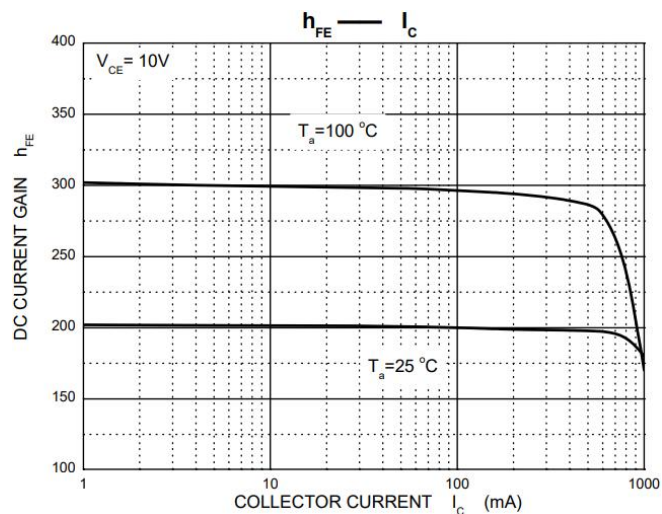
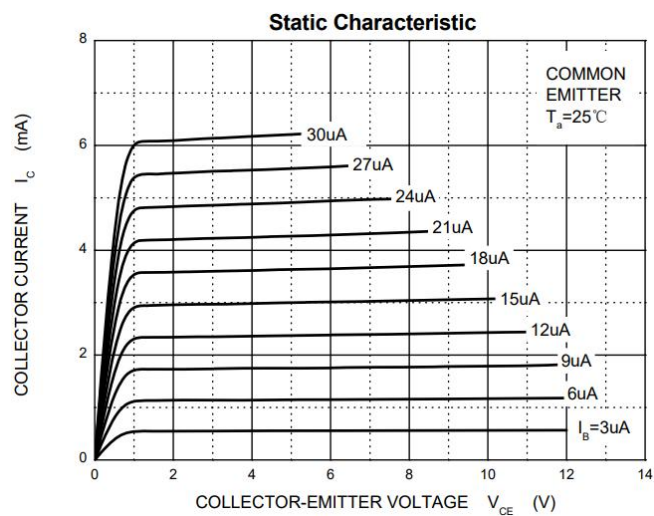
| Parameter                    | Symbol    | Limit    | Unit               |
|------------------------------|-----------|----------|--------------------|
| Collector-Base Voltage       | $V_{CBO}$ | 120      | V                  |
| Collector-Emitter Voltage    | $V_{CEO}$ | 100      | V                  |
| Emitter-Base Voltage         | $V_{EBO}$ | 5        | V                  |
| Collector Current Continuous | $I_C$     | 1        | A                  |
| Collector Power Dissipation  | $P_C$     | 250      | mW                 |
| Junction Temperature         | $T_J$     | 150      | $^{\circ}\text{C}$ |
| Storage Temperature          | $T_{STG}$ | -55~+150 | $^{\circ}\text{C}$ |

### Electrical Characteristics( $T_A=25^{\circ}\text{C}$ , unless otherwise noted.)

| Parameter                            | Symbol        | Condition                                 | Min | Typ | Max  | Unit          |
|--------------------------------------|---------------|-------------------------------------------|-----|-----|------|---------------|
| Collector-base breakdown voltage     | $V_{(BR)CBO}$ | $I_C=100\mu\text{A}, I_E=0$               | 120 |     |      | V             |
| Collector-emitter breakdown voltage  | $V_{(BR)CEO}$ | $I_C=10\text{mA}, I_B=0$                  | 100 |     |      | V             |
| Emitter-base breakdown voltage       | $V_{(BR)EBO}$ | $I_E=100\mu\text{A}, I_C=0$               | 5   |     |      | V             |
| Collector cut-off current            | $I_{CBO}$     | $V_{CB}=100\text{V}, I_E=0$               |     |     | 0.1  | $\mu\text{A}$ |
| Emitter cut-off current              | $I_{EBO}$     | $V_{EB}=4\text{V}, I_C=0$                 |     |     | 0.1  | $\mu\text{A}$ |
| DC current gain                      | hFE           | $V_{CE}=10\text{V}, I_C=1\text{mA}$       | 100 |     |      |               |
|                                      |               | $V_{CE}=10\text{V}, I_C=250\text{mA}$     | 100 |     | 300  |               |
|                                      |               | $V_{CE}=10\text{V}, I_C=0.5\text{A}$      | 60  |     |      |               |
|                                      |               | $V_{CE}=10\text{V}, I_C=1\text{A}$        | 20  |     |      |               |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C=500\text{mA}, I_B=50\text{mA}$       |     |     | 0.3  | V             |
|                                      |               | $I_C=1\text{A}, I_B=100\text{mA}$         |     |     | 0.6  |               |
| Base-emitter saturation voltage      | $V_{BE(sat)}$ | $I_C=1\text{A}, I_B=100\text{mA}$         |     |     | 1.15 | V             |
| Base-emitter voltage                 | $V_{BE(on)}$  | $V_{CE}=10\text{V}, I_C=1\text{A}$        |     |     | 1    | V             |
| Transition frequency                 | $f_T$         | $V_{CE}=10\text{V}, I_C=50\text{mA}$      | 150 |     |      | MHz           |
| Output Capacitance                   | $C_{ob}$      | $V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$ |     |     | 10   | pF            |



## Typical Characteristic

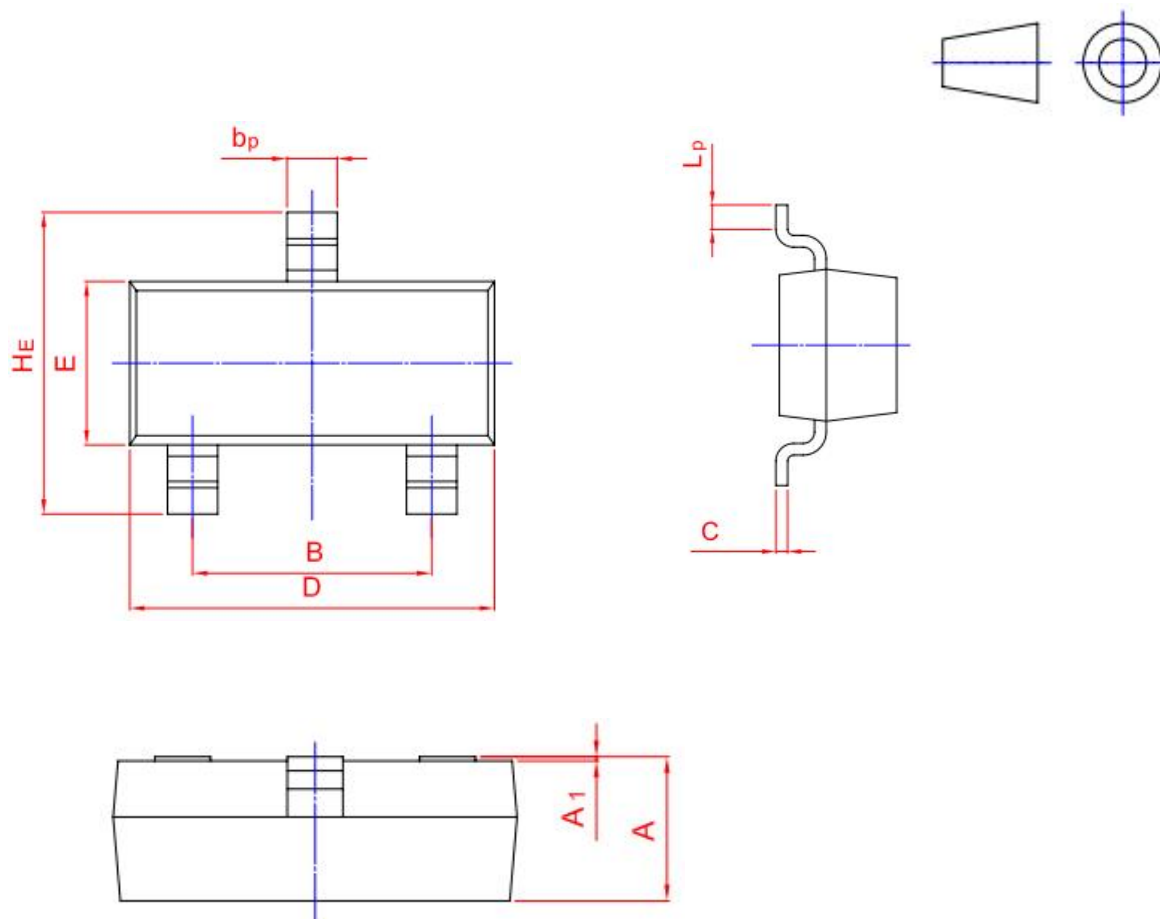




## Package Information

### SOT-23

### Dimensions in mm



| UNIT | A    | B    | $b_p$ | C    | D    | E    | $H_E$ | $A_1$ | $L_p$ |
|------|------|------|-------|------|------|------|-------|-------|-------|
| Mm   | 1.40 | 2.04 | 0.50  | 0.19 | 3.10 | 1.65 | 2.64  | 0.100 | 0.50  |
|      | 0.95 | 1.78 | 0.35  | 0.08 | 2.70 | 1.20 | 2.20  | 0.013 | 0.20  |



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